

# QM30HQ-24

DRIVE USE FOR HIGH POWER TRANSISTOR  
INSULATED TYPE

QM30HQ-24



- **IC** Collector current ..... **30A**
- **VCEX** Collector-emitter voltage ..... **1200V**
- **hFE** DC current gain ..... **5**
- **Insulated Type**
- **UL Recognized**

Yellow Card No. E80276 (N)

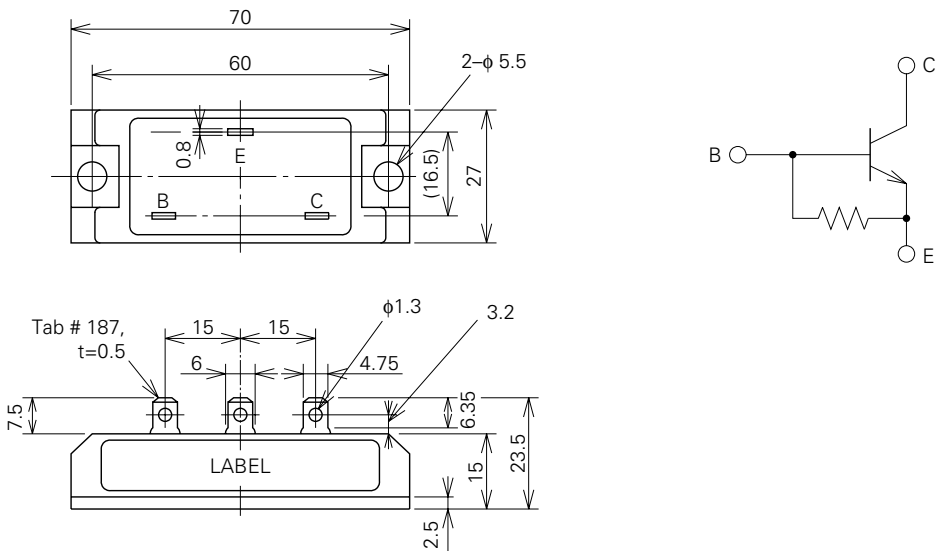
File No. E80271

## APPLICATION

Base driver for High voltage transistor modules

## OUTLINE DRAWING & CIRCUIT DIAGRAM

Dimensions in mm



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**ABSOLUTE MAXIMUM RATINGS** (T<sub>j</sub>=25°C, unless otherwise noted)

Symbol	Parameter	Conditions	Ratings	Unit
VCEX (SUS)	Collector-emitter voltage	I <sub>C</sub> =1A, V <sub>EB</sub> =2V	1200	V
VCEX	Collector-emitter voltage	V <sub>EB</sub> =2V	1200	V
VCBO	Collector-base voltage	Emitter open	1200	V
VEBO	Emitter-base voltage	Collector open	7	V
I <sub>C</sub>	Collector current	DC	30	A
P <sub>C</sub>	Collector dissipation	T <sub>C</sub> =25°C	310	W
I <sub>B</sub>	Base current	DC	6	A
T <sub>j</sub>	Junction temperature		-40~+150	°C
T <sub>stg</sub>	Storage temperature		-40~+125	°C
V <sub>iso</sub>	Isolation voltage	Charged part to case, AC for 1 minute	2500	V
—	Mounting torque	Mounting screw M5	1.47~1.96	N·m
—			15~20	kg·cm
—	Weight	Typical value	90	g

**ELECTRICAL CHARACTERISTICS** (T<sub>j</sub>=25°C, unless otherwise noted)

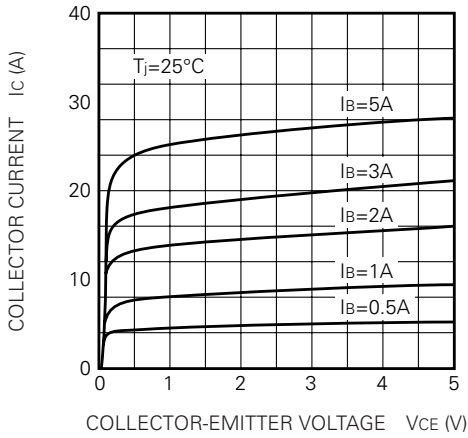
Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
I <sub>C</sub> EX	Collector cutoff current	V <sub>CE</sub> =1200V, V <sub>EB</sub> =2V	—	—	1.0	mA
I <sub>C</sub> BO	Collector cutoff current	V <sub>CB</sub> =1200V, Emitter open	—	—	1.0	mA
I <sub>E</sub> BO	Emitter cutoff current	V <sub>EB</sub> =7V	—	—	200	mA
V <sub>CE</sub> (sat)	Collector-emitter saturation voltage	I <sub>C</sub> =15A, I <sub>B</sub> =3A	—	—	1.0	V
V <sub>BE</sub> (sat)	Base-emitter saturation voltage		—	—	1.5	V
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =15A, V <sub>CE</sub> =1V	5	—	—	—
t <sub>on</sub>	Switching time	V <sub>CC</sub> =600V, I <sub>C</sub> =15A, I <sub>B1</sub> =-I <sub>B2</sub> =3A	—	—	1.5	μs
t <sub>s</sub>			—	—	7.0	μs
t <sub>f</sub>			—	—	2.0	μs
R <sub>th</sub> (j-c) Q	Thermal resistance (junction to case)	Transistor part	—	—	0.4	°C/W
R <sub>th</sub> (c-f)	Contact thermal resistance (case to fin)	Conductive grease applied	—	—	0.25	°C/W

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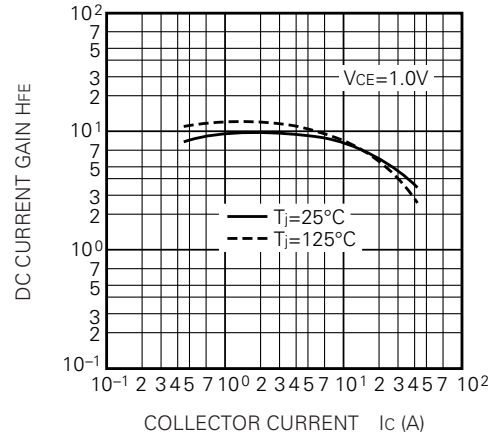
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## PERFORMANCE CURVES

**COMMON EMITTER OUTPUT CHARACTERISTICS (TYPICAL)**



**DC CURRENT GAIN VS. COLLECTOR CURRENT (TYPICAL)**



**SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)**

